



20V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
	45mΩ @ V _{GS} = 4.5V	4.9 A
20V	65mΩ @ V _{GS} = 2.5V	4.1 A

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- · Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

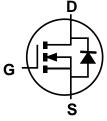
- LED Lighting
- Charging applications in portable equipment
- DC-DC Converters
- Motor Control

Mechanical Data

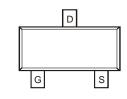
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish —Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (§3)
- Terminals Connections: See Diagram Below
- Weight: 0.009 grams (Approximate)



Top View



Internal Schematic



Top View

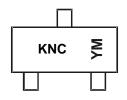
Ordering Information (Note 5)

Part Number	Case	Packaging	
ZXMN2F30FHQTA	SOT23	3,000/Tape & Reel	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/quality/product_compliance_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



KNC = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: D = 2016) M = Month (ex: 9 = September)

Date Code Key

Year	2016		2017	2018		2019	2020		2021	2022		2023
Code	D		Е	F		G	Н		I	J		K
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Drain-Source Voltage		V_{DSS}	20	V	
Gate-Source Voltage		V_{GSS}	±12	V	
Continuous Drain Current (Note 7) $V_{GS} = 4.5V$ Steady $T_A = +25^{\circ}C$ State $T_A = +70^{\circ}C$			ΙD	4.9 4.0	Α
Maximum Continuous Body Diode Forward Curre	ent (Note 7)	I _S	1.6	Α	
Pulsed Drain Current (10µs pulse, duty cycle = 1	%)	I _{DM}	22.6	Α	

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 6)		P_{D}	0.96	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	131	°C/W
Total Power Dissipation (Note 7)		P _D	1.4	W
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	$R_{\theta JA}$	89	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

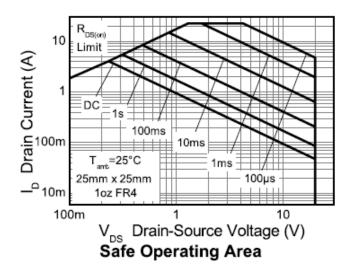
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Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 8)								
Drain-Source Breakdown Voltage	BV_{DSS}	20	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$		
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	-	-	1	μA	$V_{DS} = 20V$, $V_{GS} = 0V$		
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$		
ON CHARACTERISTICS (Note 8)								
Gate Threshold Voltage	$V_{GS(TH)}$	0.6	0.9	1.5	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$		
Static Drain-Source On-Resistance			-	45	mΩ	$V_{GS} = 4.5V, I_D = 2.5A$		
Static Drain-Source On-Nesistance	R _{DS(ON)}	-	-	65	11122	$V_{GS} = 2.5V, I_D = 2.0A$		
Diode Forward Voltage	V_{SD}	-	0.75	1.2	V	$V_{GS} = 0V, I_{S} = 1.25A$		
DYNAMIC CHARACTERISTICS (Note 9)								
Input Capacitance	C _{iss}	-	452	-	pF	101/11/		
Output Capacitance	Coss	-	102	-	pF	$V_{DS} = 10V, V_{GS} = 0V$ - f = 1.0MHz		
Reverse Transfer Capacitance	C _{rss}	-	58	-	pF	1 = 1.0WH IZ		
Total Gate Charge	Q_g	-	4.8	-	nC			
Gate-Source Charge	Q_{gs}	-	1	-	nC	$V_{DS} = 10V$, $V_{GS} = 4.5V$, $I_{D} = 3.5A$		
Gate-Drain Charge	Q_{gd}	-	1.2	-	nC			
Turn-On Delay Time	t _{D(ON)}	-	2.9	-	ns			
Turn-On Rise Time	t _R	-	5.6	-	ns	$V_{DS} = 10V, V_{GS} = 4.5V,$		
Turn-Off Delay Time	t _{D(OFF)}	-	19.4	-	ns	$R_G = 6\Omega$, $I_D = 1A$		
Turn-Off Fall Time	t _F	-	10.2	-	ns			

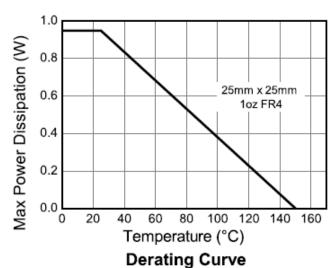
Notes:

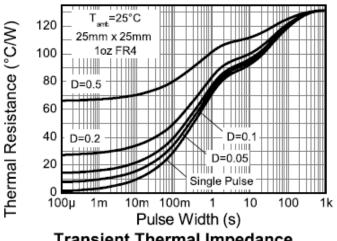
- Device mounted on FR-4 PCB, with minimum recommended pad layout.
 Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
 Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to product testing.

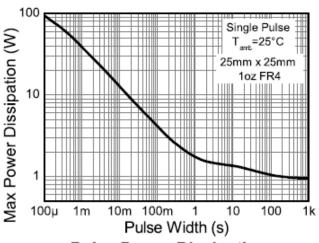


Thermal characteristics







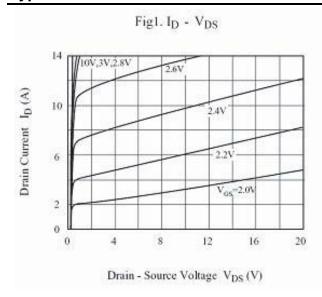


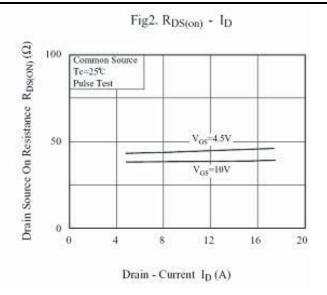
Transient Thermal Impedance

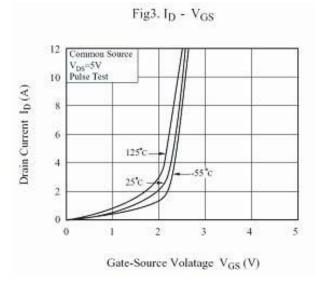
Pulse Power Dissipation

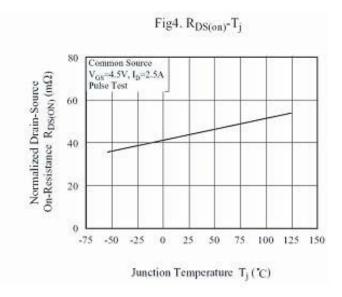


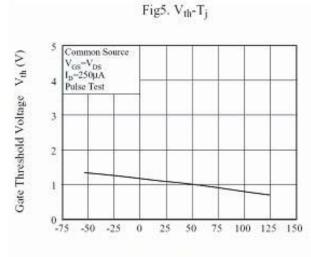
Typical Characteristics

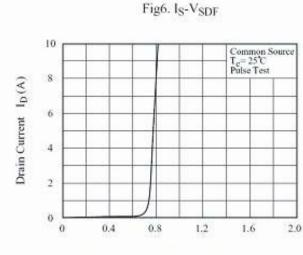












Junction Temperature Ti (C)

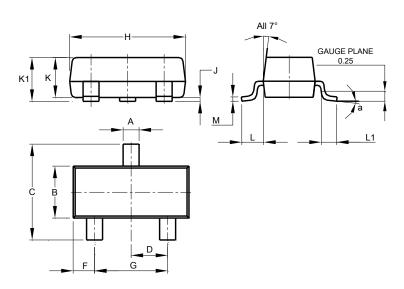
Source - Drain Forward Voltage V_{SDF} (V)



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

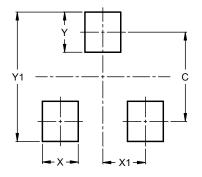


SOT23								
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
K	0.890	1.00	0.975					
K1	0.903	1.10	1.025					
L	0.45	0.61	0.55					
L1	0.25	0.55	0.40					
M	0.085	0.150	0.110					
а	0°	8°						
All Dimensions in mm								

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	29



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